

Liangliang Zhang

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

552
citations

687363

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661
citing authors

#	ARTICLE	IF	CITATIONS
1	Thermal behavior and flame retardancy of poplar wood impregnated with furfuryl alcohol catalyzed by boron/phosphorus compound system. <i>Industrial Crops and Products</i> , 2022, 176, 114361.	5.2	28
2	Combustion behavior of furfurylated wood in the presence of montmorillonite and its char characteristics. <i>Wood Science and Technology</i> , 2022, 56, 623-648.	3.2	6
3	Dimensional stability and decay resistance of clay treated, furfurylated, and clay-reinforced furfurylated poplar wood. <i>Holzforschung</i> , 2022, 76, 256-267.	1.9	4
4	Motion planning in complex urban environments: An industrial application on autonomous last-mile delivery vehicles. <i>Journal of Field Robotics</i> , 2022, 39, 1258-1285.	6.0	2
5	Montmorillonite-catalyzed furfurylated wood for flame retardancy. <i>Fire Safety Journal</i> , 2021, 121, 103297.	3.1	26
6	Autonomous Last-Mile Delivery Vehicles in Complex Traffic Environments. <i>Computer</i> , 2020, 53, 26-35.	1.1	18
7	Evolution of extractive composition in thermally modified Scots pine during artificial weathering. <i>Holzforschung</i> , 2019, 73, 747-755.	1.9	6
8	Pyrolysis and its mechanism of organomontmorillonite (OMMT) influenced by different functional groups. <i>Journal of Thermal Analysis and Calorimetry</i> , 2019, 137, 1-10.	3.6	30
9	Interfacial Cation-Defect Charge Dipoles in Stacked $\text{TiO}_2/\text{Al}_2\text{O}_3$ Gate Dielectrics. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 5140-5146.	8.0	10
10	Paraffin/wood flour/high-density polyethylene composites for thermal energy storage material in buildings: A morphology, thermal performance, and mechanical property study. <i>Polymer Composites</i> , 2018, 39, E1643.	4.6	21
11	Interface Defect Hydrogen Depassivation and Capacitance Voltage Hysteresis of $\text{Al}_2\text{O}_3/\text{InGaAs}$ Gate Stacks. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 7819-7825.	8.0	13
12	Electrochemical impedance spectroscopy for quantitative interface state characterization of planar and nanostructured semiconductor-dielectric interfaces. <i>Nanotechnology</i> , 2017, 28, 415704.	2.6	7
13	Interface Engineering for Atomic Layer Deposited Alumina Gate Dielectric on SiGe Substrates. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 19110-19118.	8.0	34
14	Border trap reduction in $\text{Al}_2\text{O}_3/\text{InGaAs}$ gate stacks. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	23
15	Selective Passivation of GeO_2/Ge Interface Defects in Atomic Layer Deposited High- k MOS Structures. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 20499-20506.	8.0	66
16	EOT Scaling of $\text{TiO}_2/\text{Al}_2\text{O}_3$ on Germanium pMOSFETs and Impact of Gate Metal Selection. <i>IEEE Electron Device Letters</i> , 2013, 34, 732-734.	3.9	21
17	Germanium Channel P-Mosfet with $\text{TiO}_2/\text{Al}_2\text{O}_3$ Bilayer High-K Gate Stacks and Solutions for Metal/ TiO_2 Interface Stability. , 2012, , .		2
18	Characterization and analysis of gate-all-around Si nanowire transistors for extreme scaling. , 2011, , .		21

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19	HCI and NBTI induced degradation in gate-all-around silicon nanowire transistors. <i>Microelectronics Reliability</i> , 2011, 51, 1515-1520.	1.7	8
20	Negative-Bias Temperature Instability in Gate-All-Around Silicon Nanowire MOSFETs: Characteristic Modeling and the Impact on Circuit Aging. <i>IEEE Transactions on Electron Devices</i> , 2010, 57, 3442-3450.	3.0	11
21	Challenges of 22 nm and beyond CMOS technology. <i>Science in China Series F: Information Sciences</i> , 2009, 52, 1491-1533.	1.1	38
22	Experimental Investigations on Carrier Transport in Si Nanowire Transistors: Ballistic Efficiency and Apparent Mobility. <i>IEEE Transactions on Electron Devices</i> , 2008, 55, 2960-2967.	3.0	66
23	A comprehensive study on Schottky barrier nanowire transistors (SB-NWTs): Principle, physical limits and parameter fluctuations. , 2008, , .		1
24	Analog/RF Performance of Si Nanowire MOSFETs and the Impact of Process Variation. <i>IEEE Transactions on Electron Devices</i> , 2007, 54, 1288-1294.	3.0	90